

# Schottky barrier diode

## RB160L-40

### ●Applications

High frequency rectification  
For switching power supply.

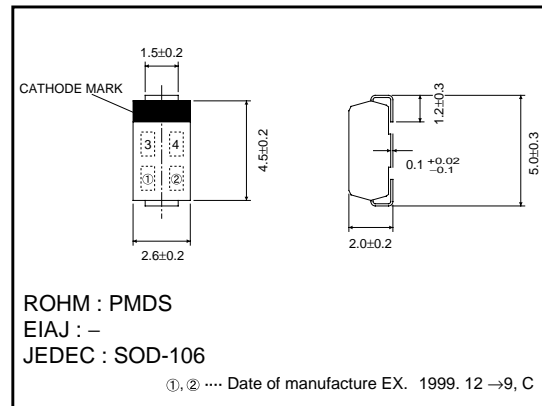
### ●Features

- 1) Compact power mold type (PMDS)
- 2) Low  $I_R$ . ( $I_R=5\text{mA Typ.}$ )
- 3) High reliability

### ●Construction

Silicon epitaxial Planar

### ●External dimensions (Units : mm)



### ●Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	40	V
DC reverse voltage	$V_R$	40	V
Mean rectifying current *	$I_o$	1	A
Peak forward surge current	$I_{FSM}$	70	A
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40~+125	$^\circ\text{C}$

\*When mounted on a PCBs board

### ●Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	0.55	V	$I_F = 1.0\text{A}$
Reverse current	$I_R$	-	-	0.1	mA	$V_R = 40\text{V}$

Diodes

● Electrical characteristic curves ( $T_a = 25^\circ\text{C}$ )

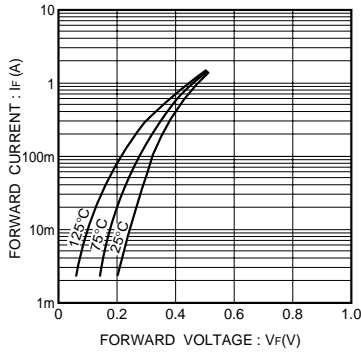


Fig. 1 Forward characteristics

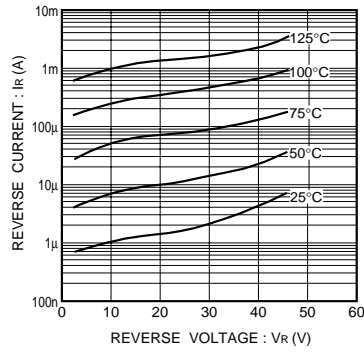


Fig. 2 Reverse characteristics

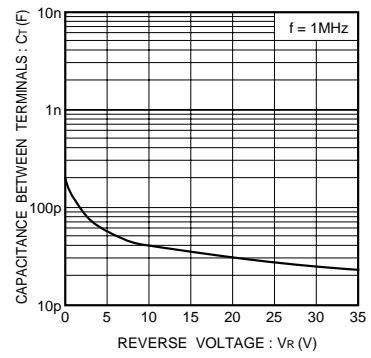


Fig. 3 Capacitance between terminals characteristics

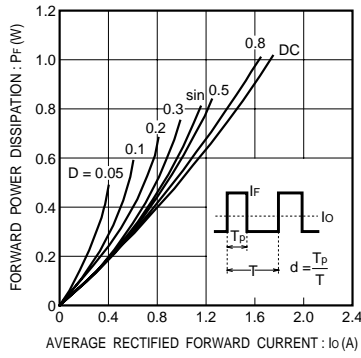


Fig. 4 Forward power dissipation characteristics

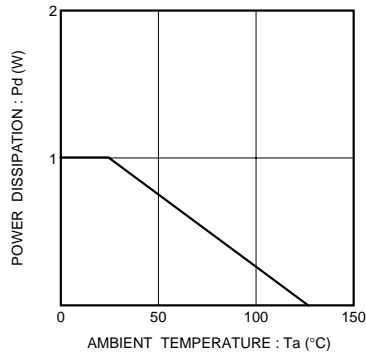


Fig. 5 Derating curve

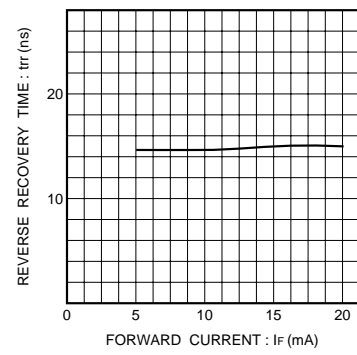


Fig. 6 Reverse recovery time characteristics